

## Silicon NPN Power Transistors

2SC1368

## DESCRIPTION

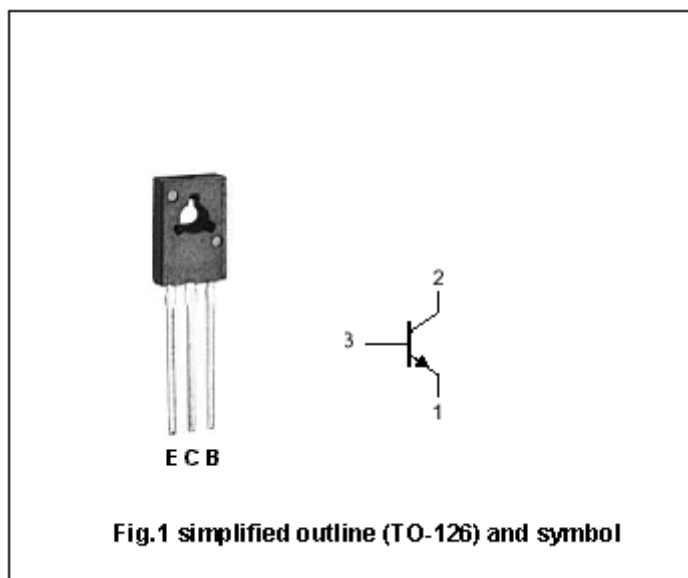
- With TO-126 package
- Low collector saturation voltage

## APPLICATIONS

- For low frequency power amplifier applications

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	25	V
$V_{CEO}$	Collector-emitter voltage	Open base	25	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		1.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	8	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA; I <sub>B</sub> =0	25			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =50 μ A; I <sub>E</sub> =0	25			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =50 μ A; I <sub>B</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =1.5A; I <sub>B</sub> =0.15A			0.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =25V; I <sub>E</sub> =0			1.0	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			1.0	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =2V	60		320	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.5A ; V <sub>CE</sub> =5V		180		MHz

PACKAGE OUTLINE

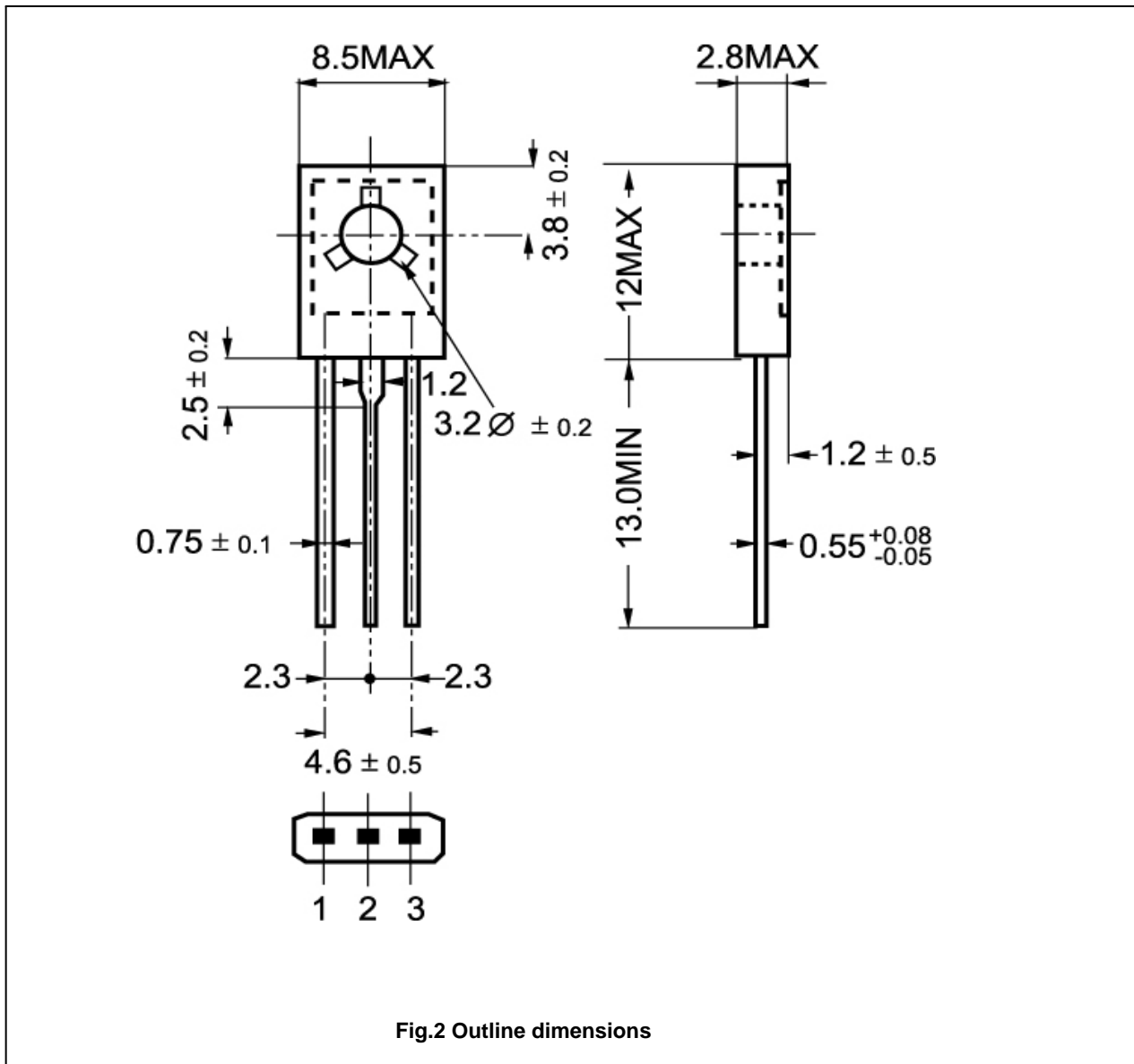


Fig.2 Outline dimensions